

ABSTRACT

Disclosed is a method for forming a micro pattern. After a dual
5 photoresist film having different glass transition temperatures is coated, an
exposure process and a wet development process are implemented to form a
dual photoresist film pattern. A RFP is then implemented for the dual
photoresist film pattern. Therefore, it is possible to prohibit warpage of the
photoresist film pattern. Accordingly, the uniformity of the critical
10 dimension and a pattern shape could be improved. A good uniformity of the
critical dimension and a good pattern shape in the etch process could be thus
implemented.